

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A manufacturing method of a display device comprising:

selectively forming a pattern comprising a composition which is emitted by use of droplet emitting means over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger;

baking the pattern; and

carrying out plasma processing to the baked pattern by use of atmospheric plasma processing means,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed in a line form, and

wherein the atmospheric plasma processing means comprises plasma generating means under 5 Torr to 800 Torr.

2. (Previously Presented) A manufacturing method of a display device comprising:

forming a transistor over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger, the transistor comprising a gate electrode, a gate insulating film, and a semiconductor layer that has a source region, a drain region, and a channel region; and

forming a pixel electrode that is electrically connected to one of the source region and the drain region,

wherein the gate electrode is formed by:

selectively forming a pattern including a metal material by use of droplet emitting means;

selectively forming a resist by use of droplet emitting means, over the pattern;

etching the pattern by use of atmospheric plasma; and

ashing the resist by use of atmospheric plasma processing means after etching the pattern,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed in a line form, and

wherein the atmospheric plasma processing means comprises plasma generating means under 5 Torr to 800 Torr.

3. (Previously Presented) A manufacturing method of a display device comprising:

forming a transistor over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger, the transistor comprising a gate electrode, a gate insulating film, a source electrode, a drain electrode, and a semiconductor layer that has a source region, a drain region, and a channel region; and

forming a pixel electrode that is electrically connected to one of the source region and the drain region,

wherein the source electrode and the drain electrode are formed by:

selectively forming a pattern including a metal material by use of droplet emitting means;

selectively forming a resist by use of droplet emitting means;

etching the pattern by use of atmospheric plasma processing means; and

ashing the resist by use of atmospheric plasma processing means,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed in a line form, and

wherein the atmospheric plasma processing means comprises plasma generating means under 5 Torr to 800 Torr.

4. (Previously Presented) A manufacturing method of a display device comprising:

selectively forming a pattern comprising a composition which is emitted by use of droplet emitting means over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger;

baking the pattern; and

carrying out plasma processing to the baked pattern by use of plasma processing means for carrying out local plasma processing,

wherein the droplet emitting means comprises a droplet emitting head in which one or a plurality of droplet emitting holes are disposed, and

wherein the plasma processing means for carrying out local plasma processing comprises plasma generating means under 5 Torr to 800 Torr.

5. (Previously Presented) A manufacturing method of a display device comprising:

forming a transistor over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger, the transistor comprising a gate electrode, a gate insulating film, and a semiconductor layer that has a source region, a drain region, and a channel region; and

forming a pixel electrode that is electrically connected to one of the source region and the drain region,

wherein the gate electrode is formed by:

selectively forming a pattern including a metal material by use of droplet emitting means;

selectively forming a resist by use of droplet emitting means, over the pattern;

etching the pattern by use of atmospheric plasma for carrying out local plasma processing; and

ashing the resist by use of plasma processing means for carrying out local plasma processing, after etching the pattern,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed, and

wherein the plasma processing means for carrying out local plasma processing comprises plasma generating means under 5 Torr to 800 Torr.

6. (Previously Presented) A manufacturing method of a display device comprising:

forming a transistor over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger, the transistor comprising a gate electrode, a gate insulating film, a source electrode, a drain electrode, and a semiconductor layer that has a source region, a drain region, and a channel region; and

forming a pixel electrode that is electrically connected to one of the source region and the drain region,

wherein the source electrode and the drain electrode are formed by:

selectively forming a pattern including a metal material by use of a droplet emitting means;

selectively forming a resist by use of a droplet emitting means, over the pattern;

etching the pattern by use of plasma processing means for carrying out local plasma processing; and

ashing the resist by use of plasma processing means for carrying out local plasma processing, after etching the pattern,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed, and

wherein the plasma processing means for carrying out local plasma processing comprises plasma generating means under 5 Torr to 800 Torr.

7.-13. (Canceled)

14. (Previously Presented) A manufacturing method of a display device comprising:

forming a transistor over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger, the transistor comprising a gate electrode, a gate insulating film, a source electrode, a drain electrode, and a semiconductor layer that has a source region, a drain region, and a channel region; and

forming a pixel electrode that is electrically connected to one of the source region and the drain region,

wherein the gate electrode is formed by:

selectively forming a first pattern including a metal material by use of droplet emitting means;

selectively forming a first resist by use of droplet emitting means, over the first pattern;

etching the first pattern by use of atmospheric plasma; and

ashing the first resist by use of atmospheric plasma processing means after etching the first pattern,

wherein the source electrode and the drain electrode are formed by:

selectively forming a second pattern including a metal material by use of droplet emitting means;

selectively forming a second resist by use of droplet emitting means;

etching the second pattern by use of atmospheric plasma processing means;
and

ashing the second resist by use of atmospheric plasma processing means,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed in a line form, and

wherein the plasma processing means comprises plasma generating means under 5 Torr to 800 Torr.

15. (Previously Presented) A manufacturing method of a display device comprising:

forming a transistor over a substrate having a size of $1000 \times 1200 \text{ mm}^2$ or larger, the transistor comprising a gate electrode, a gate insulating film, a source electrode, a drain electrode, and a semiconductor layer that has a source region, a drain region, and a channel region; and

forming a pixel electrode that is electrically connected to one of the source region and the drain region,

wherein the gate electrode is formed by:

selectively forming a first pattern including a metal material by use of droplet emitting means;

selectively forming a first resist by use of droplet emitting means, over the first pattern;

etching the first pattern by use of atmospheric plasma for carrying out local plasma processing; and

ashing the first resist by use of plasma processing means for carrying out local plasma processing, after etching the first pattern,

wherein the source electrode and the drain electrode are formed by:

selectively forming a second pattern including a metal material by use of a droplet emitting means;

selectively forming a second resist by use of a droplet emitting means, over the second pattern;

etching the second pattern by use of plasma processing means for carrying out local plasma processing; and

ashing the second resist by use of plasma processing means for carrying out local plasma processing, after etching the second pattern,

wherein the droplet emitting means comprises a droplet emitting head in which a plurality of droplet emitting holes are disposed in a line form, and

wherein the plasma processing means comprises plasma generating means under 5 Torr to 800 Torr.

16. (Previously Presented) A manufacturing method of a display device according to claim 1, wherein the droplet comprises any one of a photosensitive resist, a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

17. (Previously Presented) A manufacturing method of a display device according to claim 2, wherein the droplet for the resist comprises a photosensitive resist, and the droplet for the pattern comprises any one of a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

18. (Previously Presented) A manufacturing method of a display device according to claim 3, wherein the droplet for the resist comprises a photosensitive resist, and the droplet for the pattern comprises any one of a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

19. (Previously Presented) A manufacturing method of a display device according to claim 4, wherein the droplet comprises any one of a photosensitive resist, a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

20. (Previously Presented) A manufacturing method of a display device according to claim 5, wherein the droplet for the resist comprises a photosensitive resist, and the droplet for the pattern comprises any one of a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

21. (Previously Presented) A manufacturing method of a display device according to claim 6, wherein the droplet for the resist comprises a photosensitive resist, and the droplet for the pattern comprises any one of a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

22.-26. (Canceled)

27. (Previously Presented) A manufacturing method of a display device according to claim 14, wherein the droplet for at least one of the first resist and the second resist comprises a photosensitive resist, and the droplet for at least one of the first pattern and the second pattern comprises any one of a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.

28. (Previously Presented) A manufacturing method of a display device according to claim 15, wherein the droplet for at least one of the first resist and the second resist comprises a photosensitive resist, and the droplet for at least one of the first pattern and the second pattern comprises any one of a paste form metal material or organic liquid solution which includes the paste form metal, a ultra-fine particle form metal material or organic liquid solution which includes the metal material.